16-Mbit (1M x 16) Pseudo Static RAM

Features

- **Wide voltage range: 2.2V–3.6V**
- **Access Time: 70 ns**
- **Ultra-low active power**
  - **Typical active current: 3 mA @ f = 1 MHz**
  - **Typical active current: 18 mA @ f = f_{max}**
- **Ultra low standby power**
- **Automatic power-down when deselected**
- **CMOS for optimum speed/power**
- **Offered in a 48-ball BGA Package**
- **Operating Temperature: –40°C to +85°C**

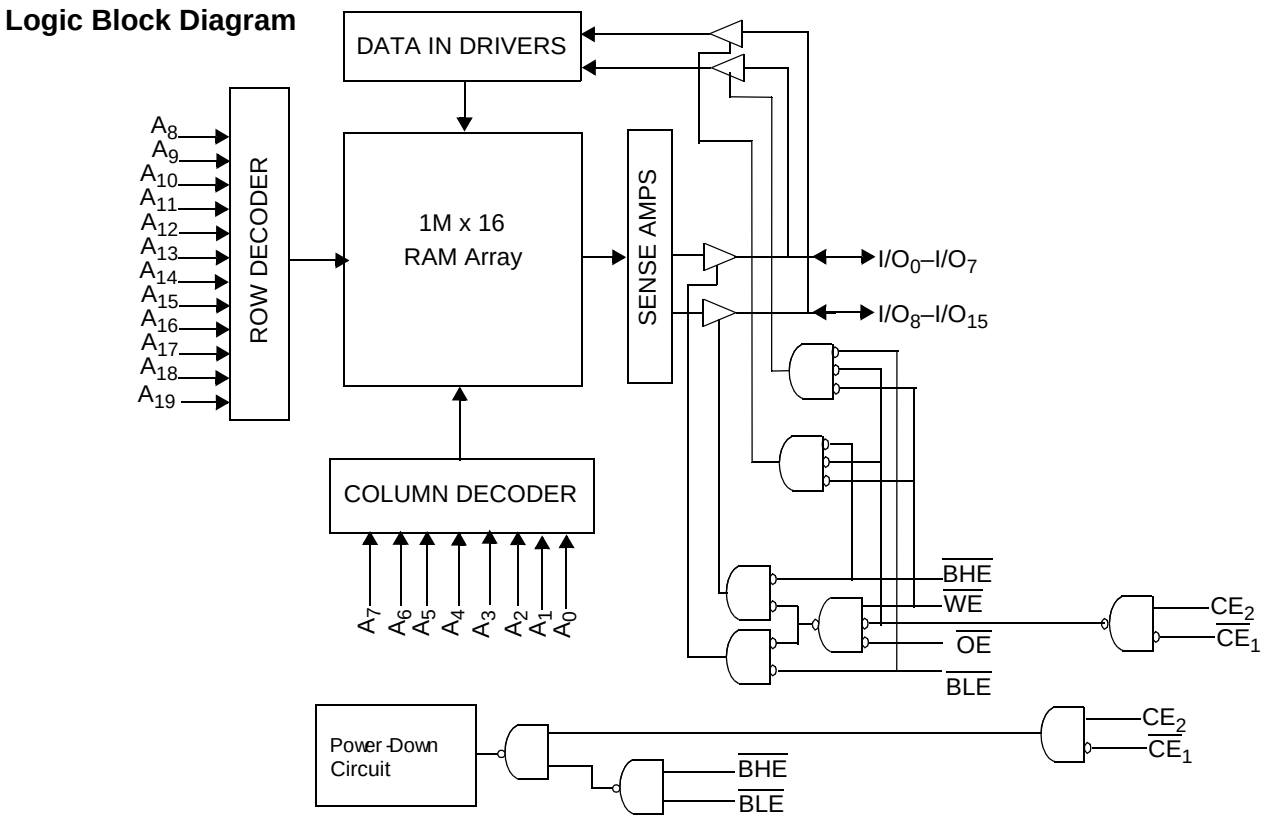
Functional Description[1]

The CYU01M16SCG is a high-performance CMOS Pseudo Static RAM organized as 1M words by 16 bits that supports an asynchronous memory interface. This device features advanced circuit design to provide ultra-low active current. This is ideal for providing More Battery Life™ (MoBL®) in portable applications such as cellular telephones. The device can be put into standby mode when deselected (CE_1 HIGH or CE_2 LOW or both BHE and BLE are HIGH). The input/output pins (I/O_0 through I/O_{15}) are placed in a high-impedance state when: deselected (CE_1 HIGH or CE_2 LOW), outputs are disabled (OE HIGH), both Byte High Enable and Byte Low Enable are disabled (BHE, BLE HIGH), or during a write operation (CE_1 LOW and CE_2 HIGH and WE LOW).

To write to the device, take Chip Enable ($\overline{CE}_1$ LOW and CE_2 HIGH) and Write Enable (WE) input LOW. If Byte Low Enable (BLE) is LOW, then data from I/O pins (I/O_0 through I/O_7), is written into the location specified on the address pins (A_0 through A_{19}). If Byte High Enable (BHE) is LOW, then data from I/O pins (I/O_8 through I/O_{15}) is written into the location specified on the address pins (A_0 through A_{19}).

To read from the device, take Chip Enables ($\overline{CE}_1$ LOW and CE_2 HIGH) and Output Enable (OE) LOW while forcing the Write Enable (WE) HIGH. If Byte Low Enable (BLE) is LOW, then data from the memory location specified by the address pins will appear on I/O_0 to I/O_7. If Byte High Enable (BHE) is LOW, then data from memory will appear on I/O_8 to I/O_{15}. Refer to the truth table for a complete description of read and write modes.

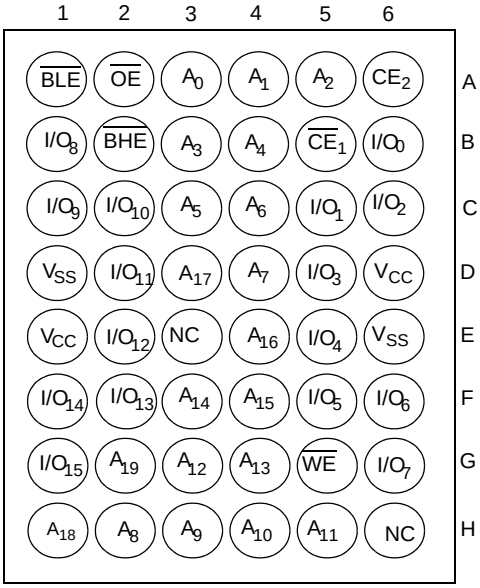
Logic Block Diagram



Note:
1. For best-practice recommendations, please refer to the Cypress application note “System Design Guidelines” on http://www.cypress.com.

Pin Configuration[2, 3]

48-Ball VFBGA
Top View

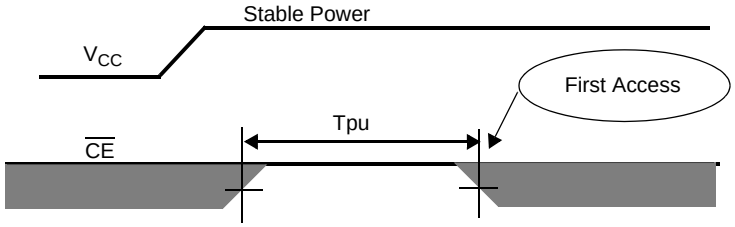


Product Portfolio[4]

Product	V_{CC} Range (V)			Speed (ns)	Power Dissipation					
					Operating I_{CC} (mA)				Standby I_{SB2} (µA)	
					f = 1MHz		f = f_{max}			
	Min.	Typ.[4]	Max.		Typ.[4]	Max.	Typ.[4]	Max.	Typ.[4]	Max.
CYU01M16SCG	2.2	3.0	3.6	70	3	5	18	25	55	70

Power-up Characteristics

The initialization sequence is shown in the figure below. Chip Select should be $\overline{CE_1}$ HIGH or CE_2 LOW for at least 200 µs after V_{CC} has reached a stable value. No access must be attempted during this period of 200 µs.



Parameter	Description	Min.	Typ.	Max.	Unit
Tpu	Chip Enable Low After Stable V_{CC}	200			µs

Notes:
2. Ball H6 and E3 can be used to upgrade to a 32-Mbit and a 64-Mbit density, respectively.
3. NC "no connect" - not connected internally to the die.
4. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at $V_{CC} = V_{CC}$ (typ) and $T_A = 25°C$. Tested initially and after design changes that may affect the parameters.

Maximum Ratings

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature .....–65°C to +150°C

Ambient Temperature with Power Applied.....–55°C to +125°C

Supply Voltage to Ground Potential.....–0.3V to V_{CCMAX} + 0.3V

DC Voltage Applied to Outputs in High Z State[5, 6, 7].....–0.3V to V_{CCMAX} + 0.3V

DC Input Voltage[5, 6, 7].....–0.3V to V_{CCMAX} + 0.3V

Output Current into Outputs (LOW).....20 mA

Static Discharge Voltage..... > 2001V (per MIL-STD-883, Method 3015)

Latch-Up Current.....> 200 mA

Device	Range	Operating Temperature (T_A)	V_{CC}
CYU01M16SCG	Industrial	–40°C to +85°C	2.2V to 3.6V

DC Electrical Characteristics (Over the Operating Range)[5, 6, 7]

Parameter	Description	Test Conditions	CYU01M16SCG-70 ns			Unit
			Min.	Typ.[4]	Max.	
V_{CC}	Supply Voltage		2.2	3.0	3.6	V
V_{OH}	Output HIGH Voltage	I_{OH} = –0.1 mA, V_{CC}= 2.2V to 3.6V	V_{CC} – 0.2			V
V_{OL}	Output LOW Voltage	I_{OL} = 0.1 mA, V_{CC}= 2.2V to 3.6V			0.2	V
V_{IH}	Input HIGH Voltage	V_{CC}= 2.2V to 3.6V	0.8 * V_{CC}		V_{CC} + 0.3V	V
V_{IL}	Input LOW Voltage	V_{CC}= 2.2V to 3.6V	–0.3		0.2 * V_{CC}	V
I_{IX}	Input Leakage Current	GND ≤ V_{IN} ≤ V_{CC}	–1		+1	µA
I_{OZ}	Output Leakage Current	GND ≤ V_{OUT} ≤ V_{CC}	–1		+1	µA
I_{CC}	V_{CC} Operating Supply Current	f = f_{MAX} = $1/t_{RC}$; V_{CC}= V_{CCmax}, I_{OUT} = 0 mA, CMOS levels		18	25	mA
		f = 1MHz		3	5	mA
I_{SB1}	Automatic CE Power-Down Current—CMOS Inputs	$\overline{CE_1}$ ≥ V_{CC} – 0.2V, CE_2 ≤ 0.2V, V_{IN} > V_{CC} – 0.2V, V_{IN} < 0.2V, f = f_{MAX} (Address and Data Only), f = 0 (OE, WE, BHE and BLE), V_{CC} = 3.60V		55	70	µA
I_{SB2}	Automatic CE Power-Down Current—CMOS Inputs	$\overline{CE_1}$ ≥ V_{CC} – 0.2V, CE_2 ≤ 0.2V, V_{IN} ≥ V_{CC} – 0.2V or V_{IN} ≤ 0.2V, f = 0, V_{CC}=V_{CCMAX}		55	70	µA

Capacitance[8]

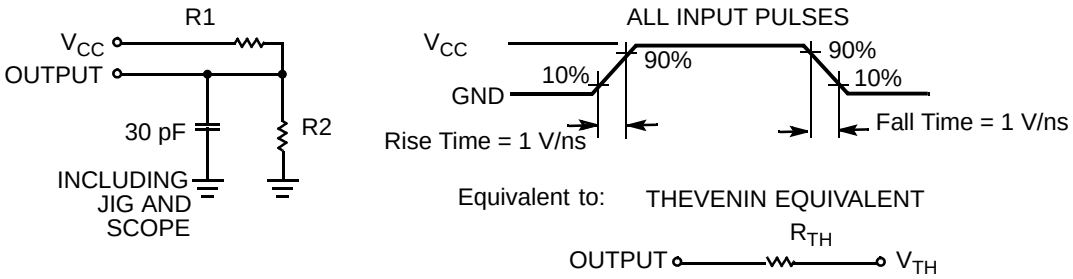
Parameter	Description	Test Conditions	Max.	Unit
C_{IN}	Input Capacitance	T_A = 25°C, f = 1 MHz, V_{CC} = $V_{CC(typ)}$	8	pF
C_{OUT}	Output Capacitance		8	pF

Thermal Resistance[8]

Parameter	Description	Test Conditions	VFBGA	Unit
Θ_{JA}	Thermal Resistance (Junction to Ambient)	Test conditions follow standard test methods and procedures for measuring thermal impedence, per EIA/JESD51	56	°C/W
Θ_{JC}	Thermal Resistance (Junction to Case)		11	°C/W

Notes:
5. $V_{IL(MIN)}$ = –0.5V for pulse durations less than 20 ns.
6. $V_{IH(Max)}$ = V_{CC} + 0.5V for pulse durations less than 20 ns.
7. Overshoot and undershoot specifications are characterized and are not 100% tested.
8. Tested initially and after any design or process changes that may affect these parameters.

AC Test Loads and Waveforms



Parameters	3.0V (V_{CC})	Unit
R1	26000	Ω
R2	26000	Ω
R_{TH}	13000	Ω
V_{TH}	1.50	V

Switching Characteristics Over the Operating Range[9, 10, 11, 14, 15]

Parameter	Description	70 ns		Unit
		Min.	Max.	
Read Cycle				
t_{RC}[13]	Read Cycle Time	70	40000	ns
t_{CD}	Chip Deselect Time $\overline{CE}_1$ = HIGH or CE_2 =LOW, $\overline{BLE}/\overline{BHE}$ High Pulse Time	15		ns
t_{AA}	Address to Data Valid		70	ns
t_{OHA}	Data Hold from Address Change	5		ns
t_{ACE}	$\overline{CE}$ LOW to Data Valid		70	ns
t_{DOE}	$\overline{OE}$ LOW to Data Valid		35	ns
t_{LZOE}	$\overline{OE}$ LOW to Low Z[10, 11, 12]	5		ns
t_{HZOE}	$\overline{OE}$ HIGH to High Z[10, 11, 12]		25	ns
t_{LZCE}	$\overline{CE}$ LOW to Low Z[10, 11, 12]	10		ns
t_{HZCE}	$\overline{CE}$ HIGH to High Z[10, 11, 12]		25	ns
t_{DBE}	$\overline{BLE}/\overline{BHE}$ LOW to Data Valid		70	ns
t_{LZBE}	$\overline{BLE}/\overline{BHE}$ LOW to Low Z[10, 11, 12]	5		ns
t_{HZBE}	$\overline{BLE}/\overline{BHE}$ HIGH to High Z[10, 11, 12]		25	ns

Notes:
9. Test conditions for all parameters other than tri-state parameters assume signal transition time of 1 ns/V, timing reference levels of $V_{CC(typ.)}/2$, input pulse levels of 0V to V_{CC}, and output loading of the specified I_{OL}/I_{OH} as shown in the "AC Test Loads and Waveforms" section.
10. At any given temperature and voltage conditions t_{HZCE} is less than t_{LZCE}, t_{HZBE} is less than t_{LZBE}, t_{HZOE} is less than t_{LZOE}, and t_{HZWE} is less than t_{LZWE} for any given device. All low-Z parameters will be measured with a load capacitance of 30 pF (3V).
11. t_{HZOE}, t_{HZCE}, t_{HZBE}, and t_{HZWE} transitions are measured when the outputs enter a high-impedance state.
12. High-Z and Low-Z parameters are characterized and are not 100% tested.
13. If invalid address signals shorter than min.tRC are continuously repeated for 40 μs, the device needs a normal read timing (t_{RC}) or needs to enter standby state at least once in every 40 μs.
14. In order to achieve 70-ns performance, the read access must be Chip Enable ($\overline{CE}_1$ or CE_2) controlled. That is, the addresses must be stable prior to Chip Enable going active.

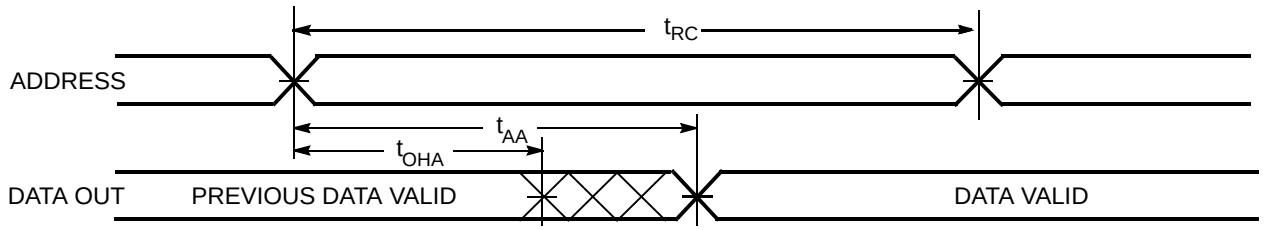
Switching Characteristics Over the Operating Range[9, 10, 11, 14, 15] (continued)

Parameter	Description	70 ns		Unit
		Min.	Max.	
Write Cycle[15]				
t_{WC}	Write Cycle Time	70	40000	ns
t_{SCE}	$\overline{CE}$ LOW to Write End	60		ns
t_{AW}	Address Set-Up to Write End	60		ns
t_{CD}	Chip Deselect Time $\overline{CE}_1$ = HIGH or CE_2 =LOW, $\overline{BLE}/\overline{BHE}$ High Pulse Time	15		ns
t_{HA}	Address Hold from Write End	0		ns
t_{SA}	Address Set-Up to Write Start	0		ns
t_{PWE}	$\overline{WE}$ Pulse Width	50		ns
t_{BW}	$\overline{BLE}/\overline{BHE}$ LOW to Write End	60		ns
t_{SD}	Data Set-Up to Write End	25		ns
t_{HD}	Data Hold from Write End	0		ns
t_{HZWE}	$\overline{WE}$ LOW to High-Z[10, 11, 12]		25	ns
t_{LZWE}	$\overline{WE}$ HIGH to Low-Z[10, 11, 12]	10		ns

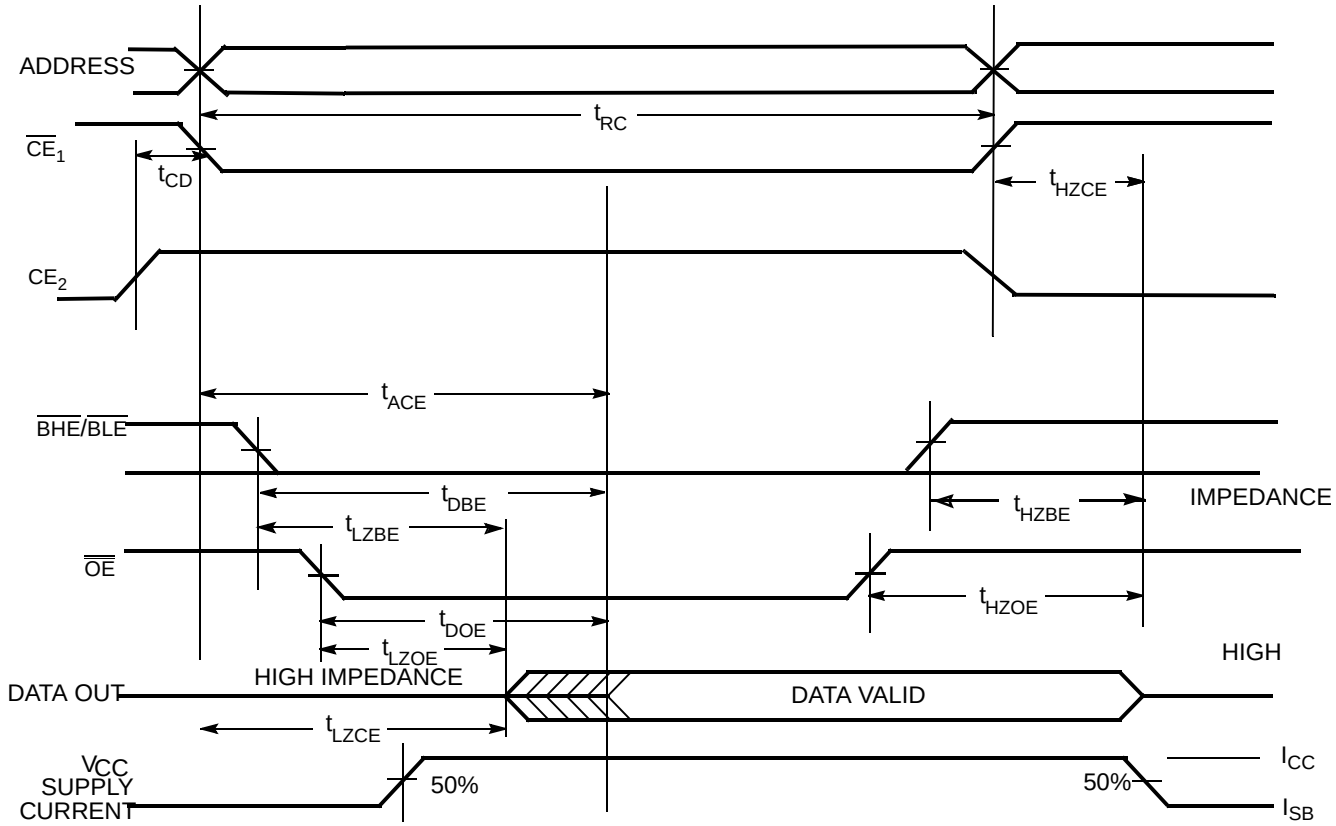
Note:
15. The internal Write time of the memory is defined by the overlap of $\overline{WE}$, $\overline{CE}_1$ = V_{IL} or CE_2 = V_{IH}, $\overline{BHE}$ and/or $\overline{BLE}$ = V_{IL}. All signals must be ACTIVE to initiate a write and any of these signals can terminate a write by going INACTIVE. The data input set-up and hold timing should be referenced to the edge of the signal that terminates the write.

Switching Waveforms

Read Cycle 1 (Address Transition Controlled)[17, 18]



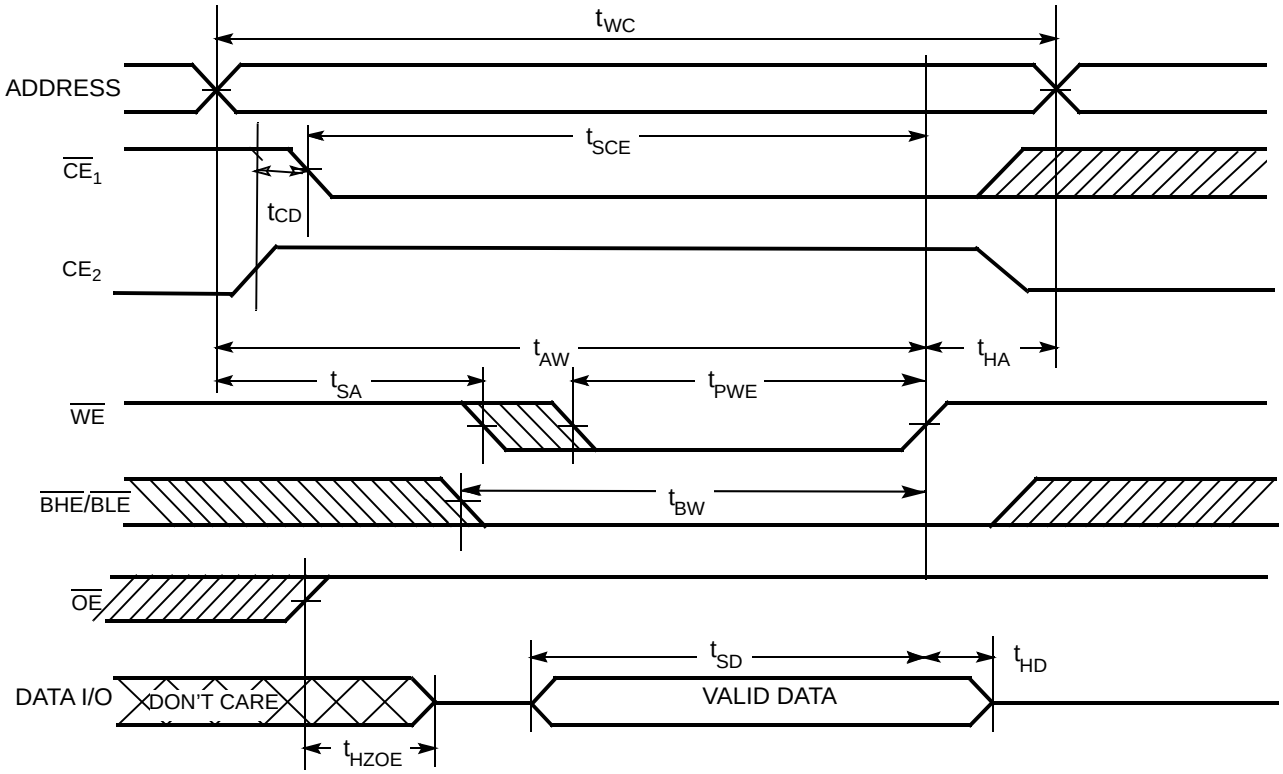
Read Cycle 2 ($\overline{OE}$ Controlled)[16, 18, 19]



Notes:
16. Whenever $\overline{CE}_1$ = HIGH or CE_2 = LOW, $\overline{BHE}/\overline{BLE}$ are taken inactive, they must remain inactive for a minimum of 5 ns.
17. Device is continuously selected. $\overline{OE}$ = $\overline{CE}_1$ = V_{IL} and CE_2 = V_{IH}.
18. $\overline{WE}$ is HIGH for Read Cycle.
19. $\overline{CE}$ is the Logical AND of $\overline{CE}_1$ and CE_2.

Switching Waveforms (continued)

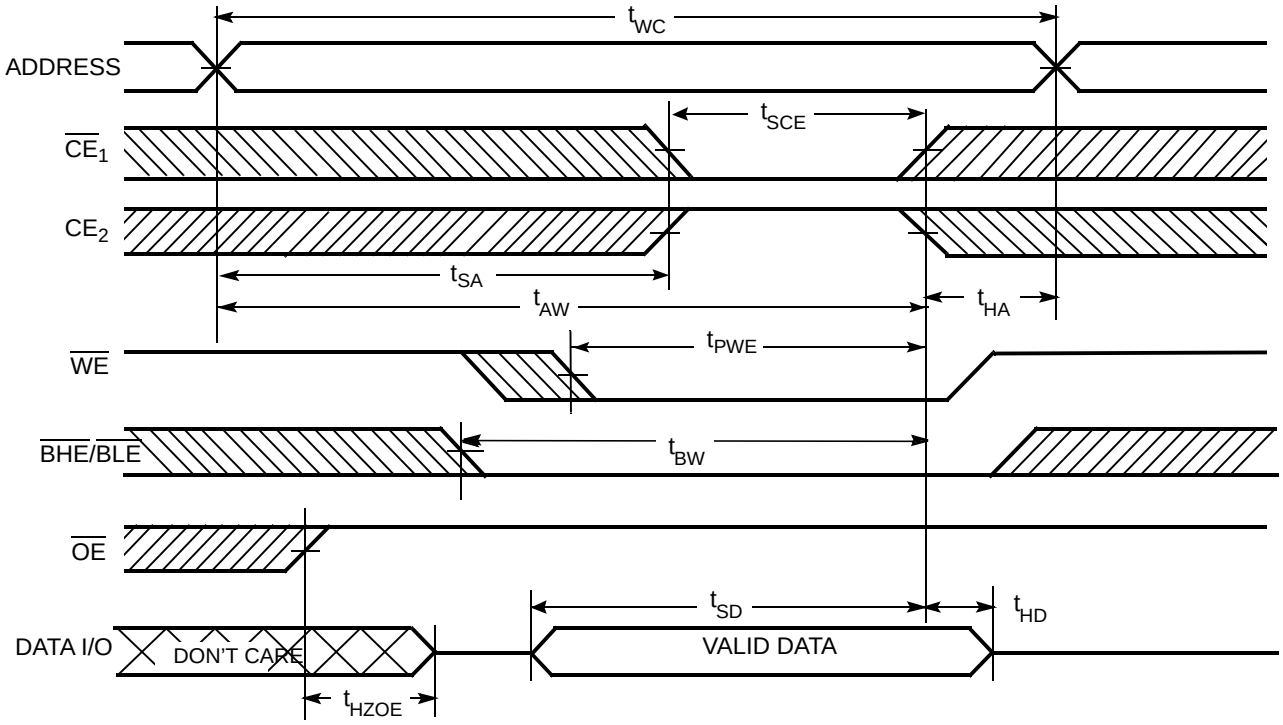
Write Cycle 1 (WE Controlled)[15, 12, 16, 19, 20, 21]



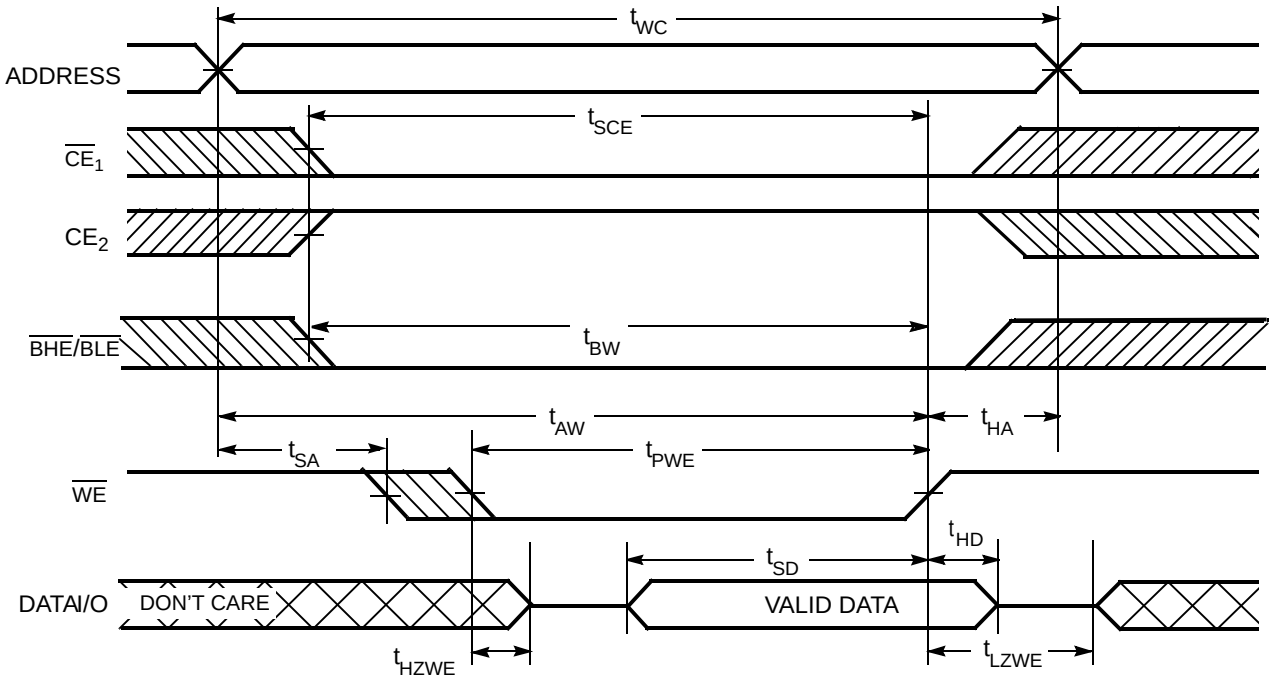
Notes:
20. Data I/O is high-impedance if $\overline{OE} \geq V_{IH}$.
21. During the DON'T CARE period in the DATA I/O waveform, the I/Os are in output state and input signals should not be applied.

Switching Waveforms (continued)

Write Cycle 2 ($\overline{CE_1}$ or CE_2 Controlled)[15, 12, 16, 20, 21]

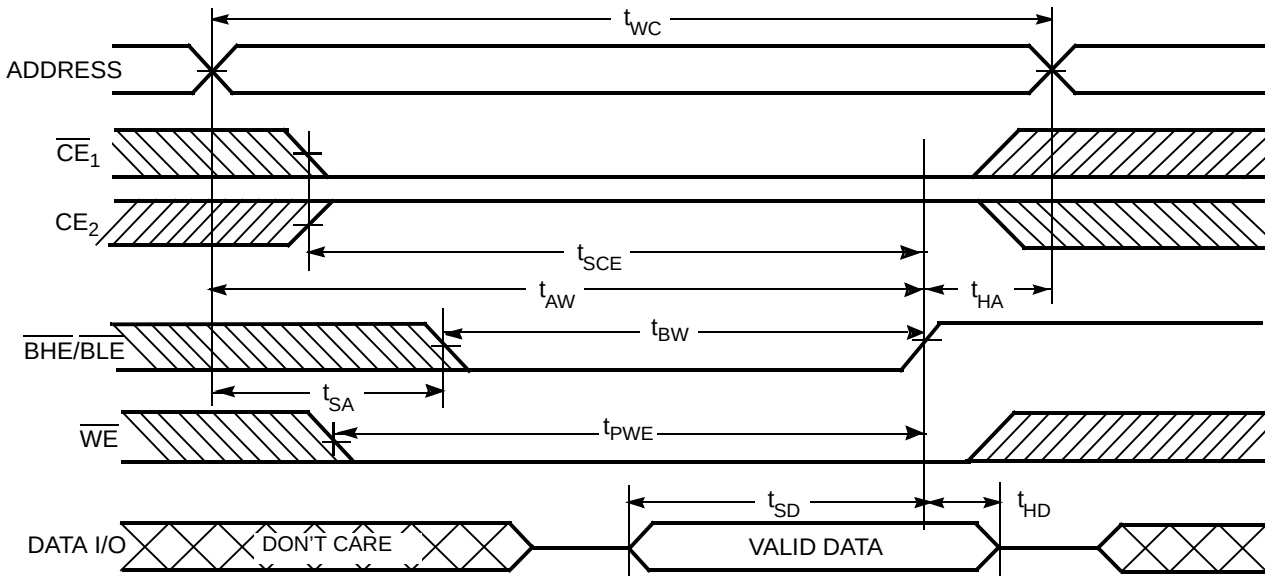


Write Cycle 3 ($\overline{WE}$ Controlled, $\overline{OE}$ LOW)[16, 21]



Switching Waveforms (continued)

Write Cycle 4 (BHE/BLE Controlled, OE LOW)[15, 16, 20, 21]



Truth Table[22]

$\overline{CE_1}$	CE_2	$\overline{WE}$	$\overline{OE}$	$\overline{BHE}$	$\overline{BLE}$	Inputs/Outputs	Mode	Power
H	X	X	X	X	X	High Z	Deselect/Power-down	Standby (I_{SB})
X	L	X	X	X	X	High Z	Deselect/Power-down	Standby (I_{SB})
X	X	X	X	H	H	High Z	Deselect/Power-down	Standby (I_{SB})
L	H	H	L	L	L	Data Out (I/O_0–I/O_{15})	Read	Active (I_{CC})
L	H	H	L	H	L	Data Out (I/O_0–I/O_7); I/O_8–I/O_{15} in High Z	Read	Active (I_{CC})
L	H	H	L	L	H	Data Out (I/O_8–I/O_{15}); I/O_0–I/O_7 in High Z	Read	Active (I_{CC})
L	H	H	H	L	L	High Z	Output Disabled	Active (I_{CC})
L	H	H	H	H	L	High Z	Output Disabled	Active (I_{CC})
L	H	H	H	L	H	High Z	Output Disabled	Active (I_{CC})
L	H	L	X	L	L	Data In (I/O_0–I/O_{15})	Write (Upper Byte and Lower Byte)	Active (I_{CC})
L	H	L	X	H	L	Data In (I/O_0–I/O_7); I/O_8–I/O_{15} in High Z	Write (Lower Byte Only)	Active (I_{CC})
L	H	L	X	L	H	Data In (I/O_8–I/O_{15}); I/O_0 –I/O_7 in High Z	Write (Upper Byte Only)	Active (I_{CC})

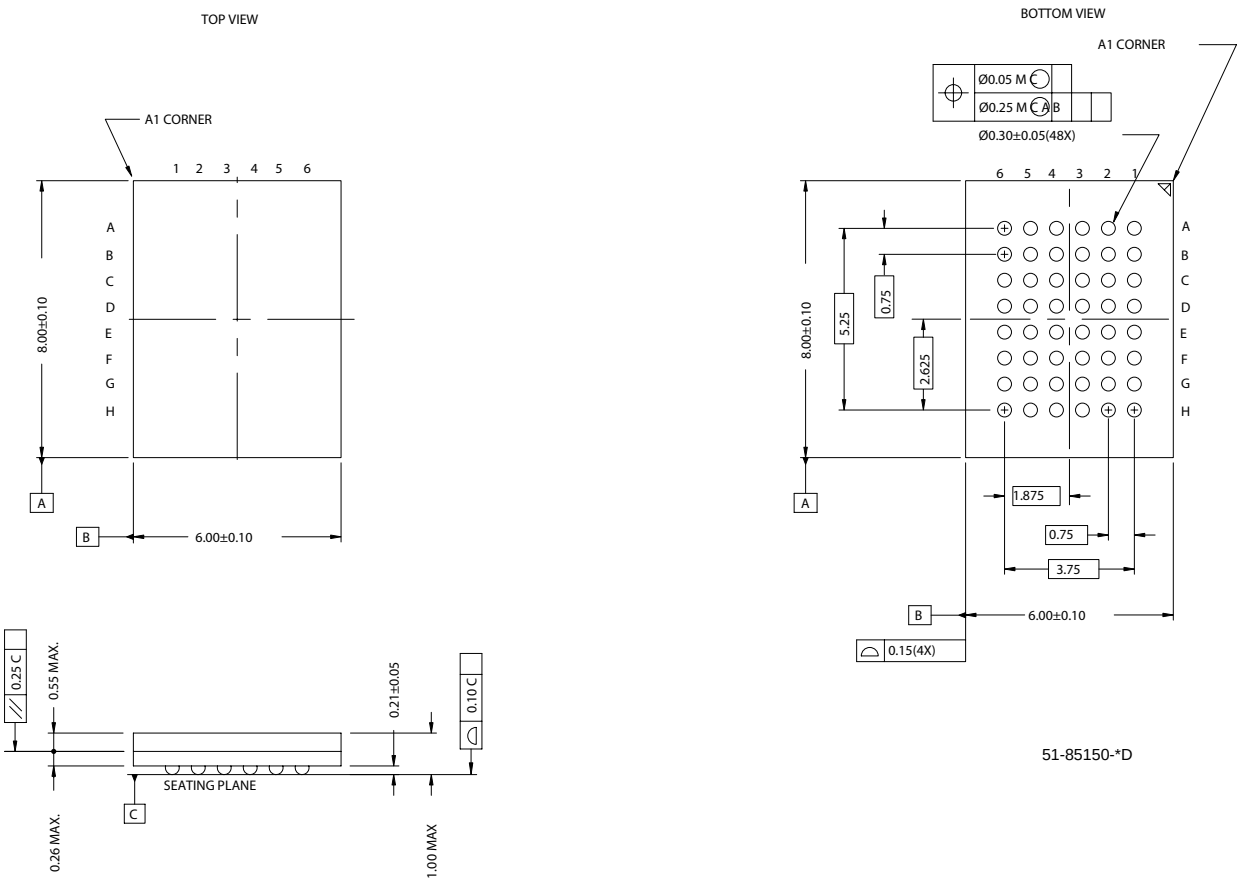
Note:
22. H = Logic HIGH, L = Logic LOW, X = Don't Care.

Ordering Information

Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
70	CYU01M16SCG-70BVXI	51-85150	48-ball Fine Pitch VBGA (6 mm × 8 mm × 1 mm) (Pb-Free)	Industrial

Package Diagram

48-ball VFBGA (6 x 8 x 1 mm) (51-85150)



Document History Page

Document Title: CYU01M16SCG MoBL3™ 16-Mbit (1M x 16) Pseudo Static RAM Document Number: 001-09739				
REV.	**ECN NO.**	**Issue Date**	**Orig. of Change**	**Description of Change**
**	497844	See ECN	NXR	New Data sheet